

## Light emitting device

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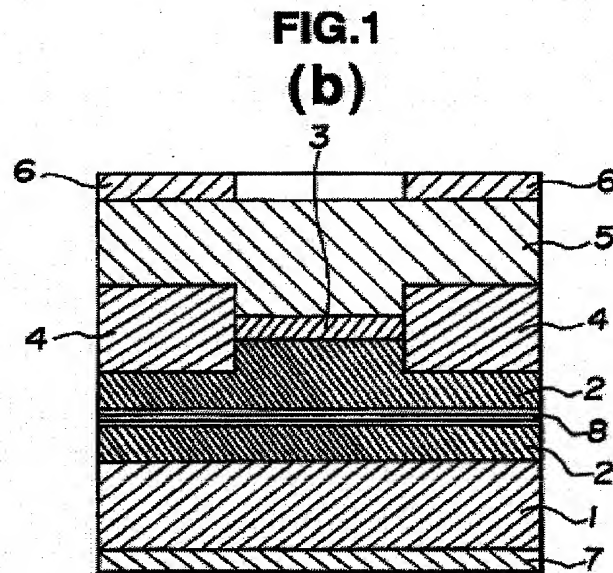
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### Abstract of DE4422660

The light emitting device comprises a first clad layer 2 and a second clad layer 5 formed successively on a semiconductor substrate 1, an active layer 3 and a current block layer 4 for current constriction both interposed between said first and second clad layers 2, 5 so as to be coplanar, a first electrode 7 formed on the surface of the substrate opposite to the first clad layer 2, and a second electrode 6 formed on the second clad layer 5. The active layer may comprise GaAs and the clad layers AlGaAs. A Bragg reflective layer 8 is disposed within the layer 2 or between the substrate and the layer 2.



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